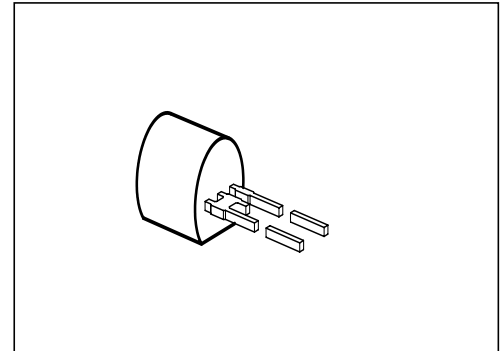


## Silicon Variable Capacitance Diode

BB 112

- For AM tuning applications
- Specified tuning range  
1 ... 8.0 V



Type	Marking	Ordering Code	Pin Configuration	Package <sup>1)</sup>
BB 112	—	Q62702-B240		TO-92

### Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse voltage	$V_R$	12	V
Forward current, $T_A \leq 60 \text{ }^\circ\text{C}$	$I_F$	50	mA
Operating temperature range	$T_{op}$	- 55 ... + 85	$^\circ\text{C}$

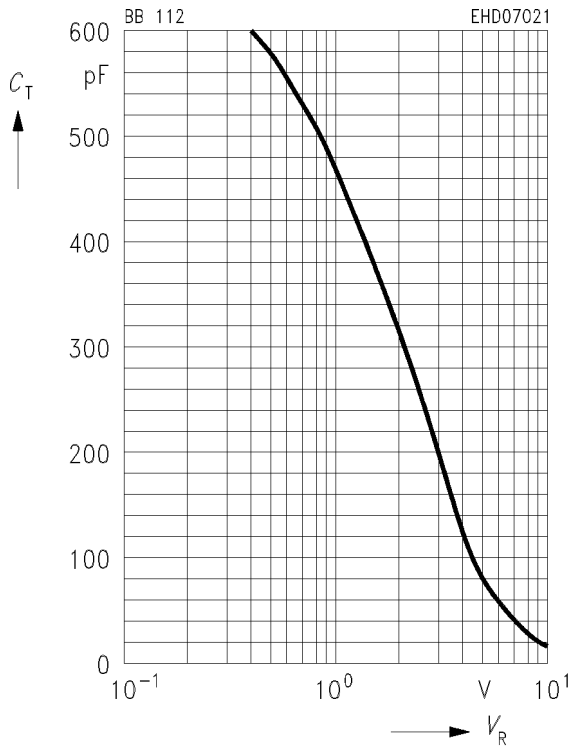
<sup>1)</sup> For detailed information see chapter Package Outlines.

## Electrical Characteristics

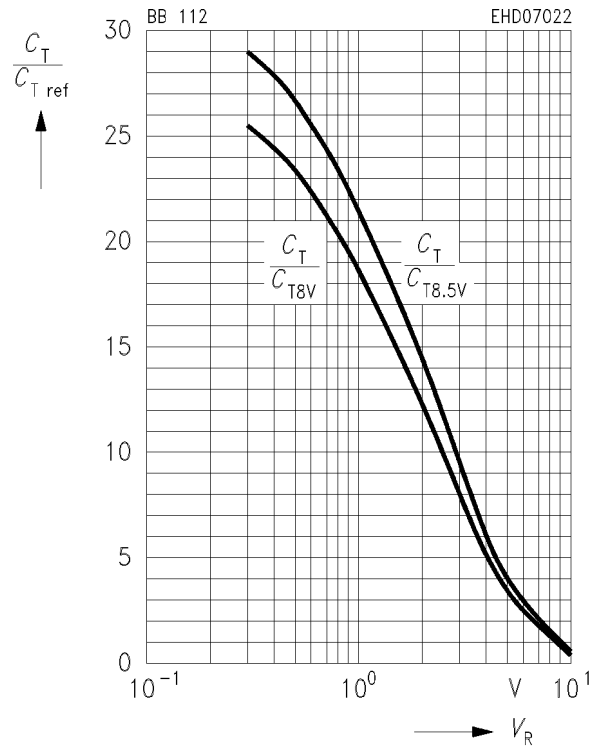
at  $T_A = 25\text{ °C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse current $V_R = 10\text{ V}$ $V_R = 10\text{ V}, T_A = 60\text{ °C}$	$I_R$	– –	– –	50 200	nA
Diode capacitance, $f = 1\text{ MHz}$ $V_R = 1\text{ V}$ $V_R = 8\text{ V}$	$C_T$	440 17.5	470 –	520 34	pF
Capacitance ratio $V_R = 1\text{ V}, 8\text{ V}$	$\frac{C_{T1}}{C_{T8}}$	15	–	–	–
Series resistance $V_R = 1\text{ V}, f = 0.5\text{ MHz}$	$r_s$	–	1.4	–	$\Omega$
Q factor $V_R = 1\text{ V}, f = 0.5\text{ MHz}$	$Q$	–	480	–	–
Temperature coefficient of diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$	$TC_C$	–	500	–	ppm/K
Capacitance matching $V_R = 1 \dots 8\text{ V}$	$\frac{\Delta C_T}{C}$	–	–	3	%

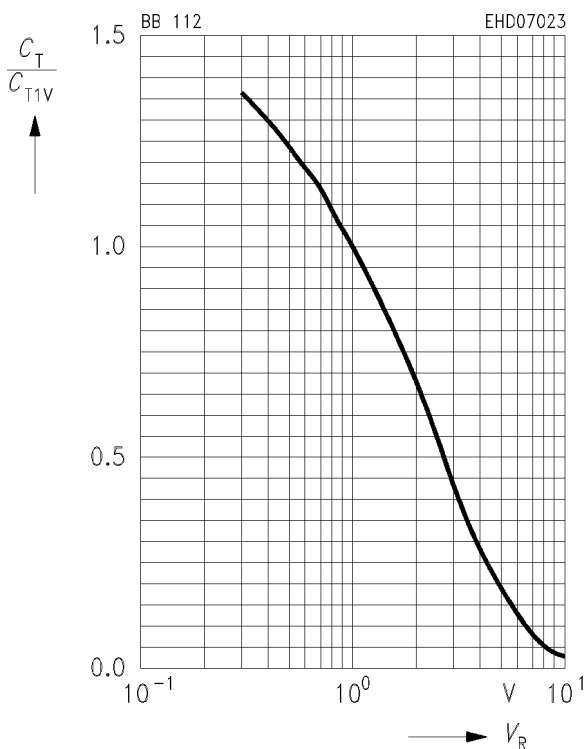
**Diode capacitance  $C_T = f(V_R)$**



**Capacitance ratio  $C_T/C_{Tref} = f(V_R)$**



**Capacitance ratio  $C_T/C_{T1V} = f(V_R)$**



**Temperature coefficient of junction capacitance  $TC_C = f(V_R)$**

